

Application No. 10/760,118

Pleas amend paragraph 0024 of the specification as follows:

[0024] In fabricating a collection mirror that incorporates the sacrificial reflective surface for EUV lithography, it is first necessary to design and deposit the underlying reflective surface or stack onto a substrate. A preferred underlying reflective surface comprises alternating bilayers described above. For EUV applications, the underlying reflective surface will typically comprise from 20 to 80 bilayers which produces a stack that should reflect approximately 20% to 80% and preferably at least 30% EUV and has a normal incidence reflectivity of EUV of at least about 30%. A preferred stack comprises 40 to 60 bilayers of Mo and Si which reflects typically 60% to 70% EUV. For EUV lithography, the expected maximum EUV reflectance from plasma-facing collection mirrors will typically be within these ranges. The EUV reflectance of the stack will not improve ~~insignificantly~~ significantly beyond this even if more bilayers are added.